SWITCHING DIODE

VOLTAGE RANGE: 35/75 VOLTS
CURRENT: 100mA

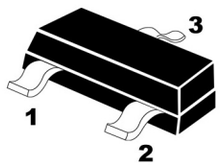
FEATURES

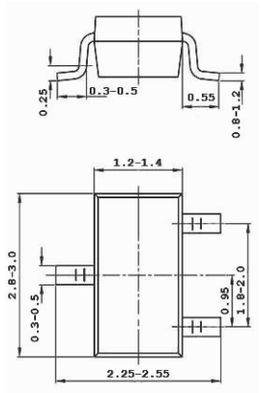
- High speed switching: trr=4.0ns(max)
- Low capacitance: C_T=2.5 pF(typ.)

MARKING: 1S2835: A3
1S2836: A41

SOT-23

1. CATHODE
2. CATHODE
3. ANODE





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Limits		UNITS
		1S2835	1S2836	
Non-Repetitive Peak Reverse Voltage	V_{RM}	35	75	V
DC Blocking Voltage	V_R	30	50	V
Average Rectified Output Current	I_O	100		mA
Power Dissipation	P_d	150		mW
Junction Temperature	T_J	125		℃
Storage Temperature Range	T_{STG}	-55~+125		℃

ELECTRICAL CHARACTERISTICS

Parameters	Symbols	Test conditions	Min.	Typ.	Max.	UNITS
Forward Voltage	V_{F1}	I_F=10mA		0.72	1.0	V
	V_{F2}	I_F=50mA		0.88	1.1	V
	V_{F3}	I_F=100mA		1.0	1.2	V
Reverse Current:1S2835	I_R	V_R=30V			0.1	μA
1S2836	I_R	V_R=50V			0.1	μA
Reverse Recovery Time	t_{rr}	I_F=10mA, V_R=6V, R_L=100Ω, I_{rr}=0.1*I_R			4.0	ns
Capacitance Between Terminals	C_T	V_R =0V, f=1MHz		2.5	4.0	pF

RoHS Pb-free TIP Semiconductor